TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K16FS

High Speed Switching Applications Analog Switch Applications

Suitable for high-density mounting due to compact package

• Low on resistance: $R_{on} = 3.0 \Omega \text{ (max) } (@V_{GS} = 4 \text{ V})$

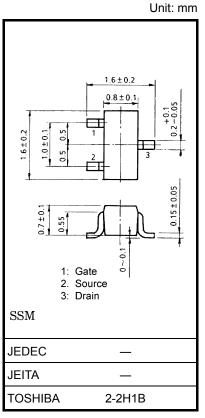
: $R_{on} = 4.0 \Omega \text{ (max) } (@V_{GS} = 2.5 \text{ V})$

: $R_{on} = 15 \Omega (max) (@V_{GS} = 1.5 V)$

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit | |
|-------------------------------------|-------|------------------|---------|------|--|
| Drain-Source voltage | | V_{DS} | 20 | V | |
| Gate-Source voltage | | V_{GSS} | ±10 | V | |
| Drain current | DC | I _D | 100 | mA | |
| | Pulse | I _{DP} | 200 | | |
| Drain power dissipation (Ta = 25°C) | | P _D | 100 | mW | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature range | | T _{stg} | -55~150 | °C | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

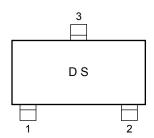


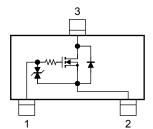
Weight: 2.4 mg (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking

Internal connections





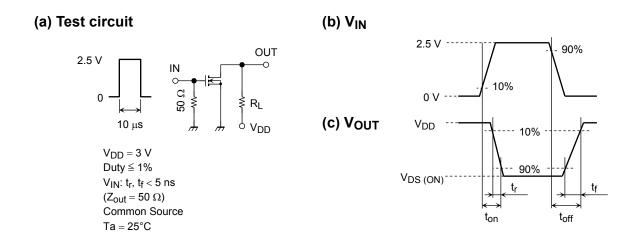
Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Electrical Characteristics (Ta = 25°C)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|---------------|----------------------|---|-----|------|-----|------|
| Gate leakage current | | I _{GSS} | $V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$ | _ | _ | ±1 | μА |
| Drain-Source breakdown voltage | | V (BR) DSS | $I_D = 0.1 \text{ mA}, V_{GS} = 0$ | 20 | _ | _ | V |
| Drain cut-off curre | ent | I _{DSS} | V _{DS} = 20 V, V _{GS} = 0 | _ | _ | 1 | μΑ |
| Gate threshold vo | ltage | V _{th} | $V_{DS} = 3 \text{ V}, I_{D} = 0.1 \text{ mA}$ | 0.6 | _ | 1.1 | V |
| Forward transfer a | admittance | Y _{fs} | $V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$ | 40 | _ | _ | mS |
| Drain-Source ON resistance | | R _{DS} (ON) | $I_D = 10$ mA, $V_{GS} = 4$ V | _ | 1.5 | 3.0 | Ω |
| | | | $I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$ | _ | 2.2 | 4.0 | |
| | | | I _D = 1 mA, V _{GS} = 1.5 V | _ | 5.2 | 15 | |
| Input capacitance | | C _{iss} | $V_{DS} = 3 V$, $V_{GS} = 0$, $f = 1 MHz$ | _ | 9.3 | _ | pF |
| Reverse transfer capacitance | | C _{rss} | $V_{DS} = 3 V$, $V_{GS} = 0$, $f = 1 MHz$ | _ | 4.5 | _ | pF |
| Output capacitance | | Coss | $V_{DS} = 3 V$, $V_{GS} = 0$, $f = 1 MHz$ | _ | 9.8 | _ | pF |
| Switching time | Turn-on time | t _{on} | $V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0~2.5 \text{ V}$ | _ | 70 | _ | ns |
| | Turn-off time | t _{off} | | _ | 125 | _ | |

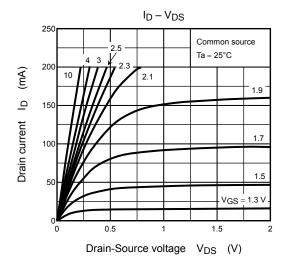
Switching Time Test Circuit

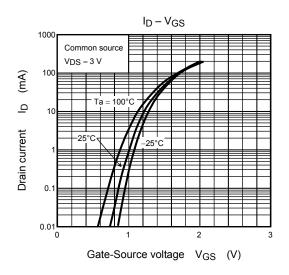


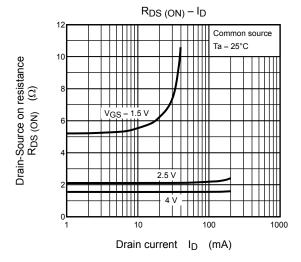
Precaution

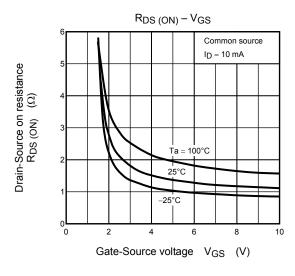
 V_{th} can be expressed as voltage between gate and source when low operating current value is I_D = 100 μA for this product. For normal switching operation, V_{GS} (on) requires higher voltage than V_{th} and V_{GS} (off) requires lower voltage than V_{th} . (Relationship can be established as follows: V_{GS} (off) < V_{th} < V_{GS} (on))

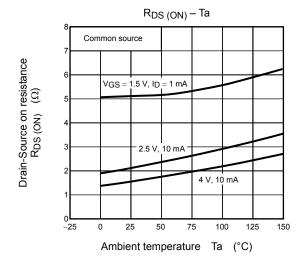
Please take this into consideration for using the device.

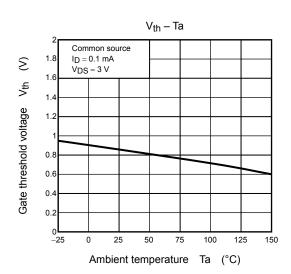




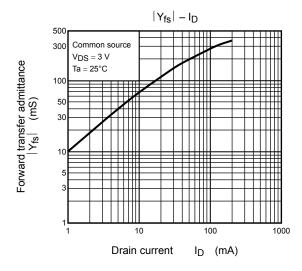


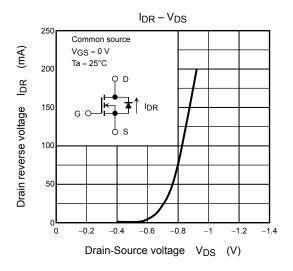


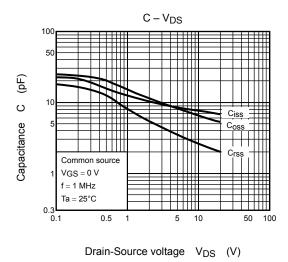


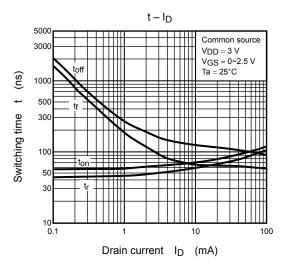


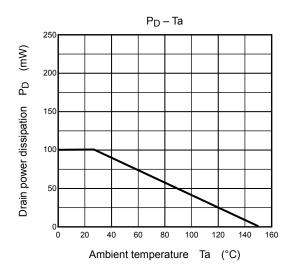
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20070701-EN GENERAL

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